

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|---|---|------------------|---------|------------------|
| S1 | 59329 | ((reactive near ion near etch\$3) RIE) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 12:59 |
| S2 | 489 | S1 same silica and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:03 |
| S3 | 17 | S1 same silica and (silicon near wafer) and plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:04 |
| S4 | 3292 | S1 same (silica (silicon near \$3oxide)) near3 (film layer coat\$3) and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:05 |
| S5 | 484 | S4 and plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:05 |
| S6 | 530 | S1 same (silica (silicon near \$3oxide)) near3 (film layer coat\$3) same (silicon semiconductor) near3 wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:08 |
| S7 | 50 | S6 and plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:05 |
| S8 | 15 | S6 same plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:08 |
| S9 | 560 | S1 same (silica (silicon near \$3oxide)) near3 (film layer coat\$3 deposit\$9) same (silicon semiconductor) near3 wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:12 |

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| S10 | 15 | S9 same plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:27 |
| S11 | 0 | S10 not S8 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:09 |
| S12 | 1643 | plasma near9 (film layer coat\$3 deposit\$9) same (silica (silicon near \$3oxide)) same (silicon semiconductor) near3 wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:13 |
| S13 | 47 | RF near9 plasma near9 (film layer coat\$3 deposit\$9) same (silica (silicon near \$3oxide)) same (silicon semiconductor) near3 wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:14 |
| S14 | 1 | S13 and RF near9 (power source) near9 connect\$3 near3 electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:17 |
| S15 | 0 | RF near9 (power source) near9 connect\$3 near3 ((substrate near3 (silicon semiconductor)) wafer electrode) same (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone polymer organopolysiloxane polyorganosiloxane) near3 (deposit layer film coat\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:20 |
| S16 | 29 | RF near9 (power source) near9 connect\$3 near3 ((substrate near3 (silicon semiconductor)) wafer electrode) and (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone polymer organopolysiloxane polyorganosiloxane) near3 (deposit layer film coat\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 14:26 |
| S17 | 139 | (RF (radio frequency)) near9 (power source) near9 ((substrate near3 (silicon semiconductor)) wafer electrode) and (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone organopolysiloxane polyorganosiloxane) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:28 |

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| S18 | 52 | S17 and plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:29 |
| S19 | 53 | (RF (radio frequency)) near9 (power source) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer electrode) and (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone organopolysiloxane polyorganosiloxane) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:37 |
| S20 | 24 | S19 and plasma same (hydrogen "H.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:29 |
| S21 | 13 | (RF (radio frequency)) near9 (power source generat\$5) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer) and plasma near9 (hydrogen "H. sub.2") same (treat\$9 harden\$9 cross\$1link\$3) near9 (silicon\$3 \$5organopolysiloxane polyorganosiloxane \$5organosiloxane) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:45 |
| S22 | 32 | (RF (radio frequency)) near9 (power source generat\$5) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer) and plasma near9 (hydrogen "H. sub.2") same (treat\$9 harden\$9 coat\$3 deposit\$9 layer film cross\$1link\$3) near9 (silicon\$3 \$5organopolysiloxane polyorganosiloxane \$5organosiloxane) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:39 |
| S23 | 15 | (RF (radio frequency)) near9 (power source generat\$5) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer) and plasma near9 (hydrogen "H. sub.2") same insulat\$5 near3 (deposit\$9 coat\$3 film layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 13:46 |
| S24 | 13 | (RF plasma) near9 (power source) near9 connect\$3 near3 ((substrate near3 (silicon semiconductor)) wafer) same (post\$1treat\$9 treat\$9 harden\$9 cross\$1link\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 14:30 |

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| S25 | 23 | (RF plasma) near9 (power source) near9 connect\$3 near3 (((substrate support) near3 (silicon semiconductor electrode)) wafer) same (post\$1treat\$9 treat\$9 harden\$9 cross\$1link\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:17 |
| S26 | 2 | "07235524" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 14:36 |
| S27 | 1247 | (RF near9 high near frequency near9 plasma) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:18 |
| S28 | 232 | (RF near9 high adj frequency near9 plasma) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:18 |
| S29 | 91 | (RF near9 high adj frequency near plasma) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:18 |
| S30 | 10 | (RF near high adj frequency near plasma) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:57 |
| S31 | 14411 | ((chemical near vapo\$1r near deposition) Cvd) near9 plasma same (silica (silicon near \$3oxide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:59 |
| S32 | 1658 | S31 same (chamber apparatus) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 15:58 |
| S33 | 830 | ((chemical near vapo\$1r near deposition) Cvd) near9 plasma near9 (chamber apparatus) same (silica (silicon near \$3oxide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:00 |
| S34 | 496 | ((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) same (silica (silicon near \$3oxide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:00 |

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| S35 | 240 | ((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) near9 (silica (silicon near \$3oxide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:00 |
| S36 | 28 | ((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) near9 (silane organosilane) same oxygen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:02 |
| S37 | 1 | ((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) near9 fig\$4 same (silane disilane methylsilane organosilane) same oxygen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:04 |
| S38 | 1 | ((chemical near vapo\$1r near deposition) Cvd) near plasma near9 fig\$4 same (silane disilane methylsilane organosilane) same oxygen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:04 |
| S39 | 19 | ((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (silane disilane methylsilane organosilane) same oxygen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:05 |
| S40 | 3 | ((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (chamber apparatus) same (silane disilane methylsilane organosilane) same oxygen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:06 |
| S41 | 24 | ((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (chamber apparatus) and (silane disilane methylsilane organosilane) same oxygen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:08 |
| S42 | 127 | ((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (device chamber apparatus) and (silane disilane methylsilane organosilane) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:12 |
| S43 | 202 | ((chemical near vapo\$1r near deposition) Cvd) near9 plasma same (power source) near9 connect\$5 near9 (substrate support) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:14 |

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| S44 | 64 | ((chemical near vapo\$1r near deposition) Cvd) near9 plasma same (power source) near3 connect\$5 near3 (substrate support) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 18:07 |
| S45 | 4 | "10004062" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:17 |
| S46 | 126 | "5314724" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 18:07 |
| S47 | 2 | "5314724".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 18:07 |